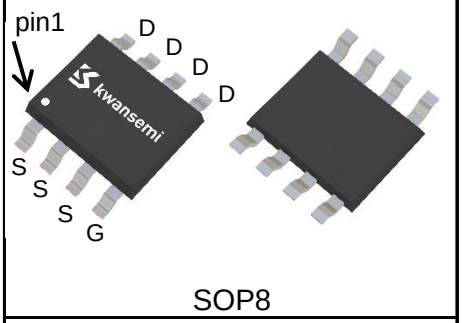
KS1210HAT

Dual N-Channel Advanced Power MOSFET

Features

- 100V/9A,
  $R_{DS\ (ON)}$ =14mΩ(Typ.)@V_{GS}=10V
  $R_{DS\ (ON)}$ =18mΩ(Typ.)@V_{GS}=4.5V
- Excellent Q_G x $R_{DS(on)}$ product(FOM)
- SGT Technology
- Fast Switching Speed
- Low Capacitance to Minimize Driver Losses

Pin Description



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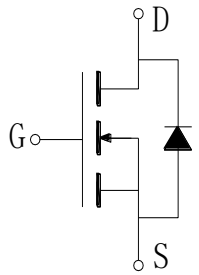


N-Channel MOSFET

Applications

- Switch Mode Power Supply

RoHS Pb HF Halogen-Free

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T_A=25°C Unless Otherwise Noted)				
V_{DSS}	Drain-Source Voltage		100	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_A=25°C	2.9	A
Mounted on Large Heat Sink				
I_{DP} ①	300μs Pulse Drain Current Tested	T_A=25°C	36	A
I_D ②	Continuous Drain Current(V_{GS}=10V)	T_A=25°C	9	A
		T_A=70°C	7.2	
P_D	Maximum Power Dissipation	T_A=25°C	2.5	W
		T_A=70°C	1.6	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead		35	°C/W
$R_{\theta JA}$ ③	Thermal Resistance-Junction to Ambient		50	°C/W
Drain-Source Avalanche Ratings				
E_{AS} ④	Avalanche Energy, Single Pulsed		25	mJ

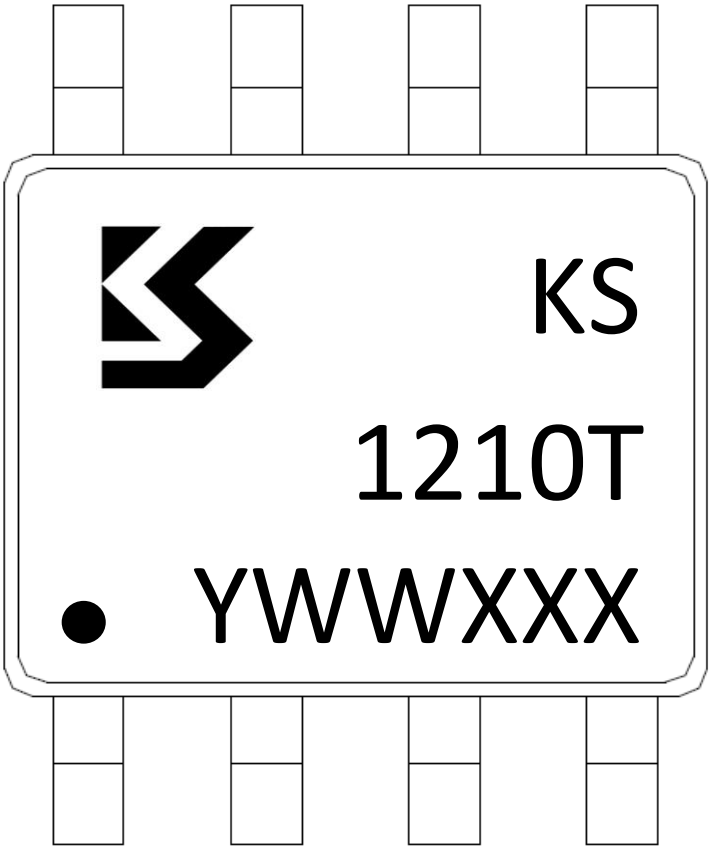
Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS1210HAT			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	100			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=100V, V_{GS}=0V			1	μA
		T_J=125°C			30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1.2	2	2.4	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$R_{DS(ON)}$ ⑤	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=10A		14	17	mΩ
		V_{GS}=4.5V, I_{DS}=8A		18	26	mΩ
Diode Characteristics						
V_{SD} ⑤	Diode Forward Voltage	I_{SD}=10A, V_{GS}=0V		0.85	1.2	V
t_{rr}	Reverse Recovery Time	I_{SD}=10A, dI_{SD}/dt=100A/μs		32		ns
Q_{rr}	Reverse Recovery Charge			43		nC
Dynamic Characteristics ⑥						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz		1.6		Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=50V, Frequency=1.0MHz		1080		pF
C_{oss}	Output Capacitance			105		
C_{rss}	Reverse Transfer Capacitance			10		
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=50V, I_{DS}=10A, V_{GEN}=10V,R_G=6Ω		6		ns
t_r	Turn-on Rise Time			12		
$t_{d(OFF)}$	Turn-off Delay Time			20		
t_f	Turn-off Fall Time			5		
Gate Charge Characteristics ⑥						
Q_g	Total Gate Charge	V_{DS}=50V, V_{GS}=10V, I_{DS}=10A		20		nC
Q_{gs}	Gate-Source Charge			4.7		
Q_{gd}	Gate-Drain Charge			4.9		

Notes:
①Pulse width limited by safe operating area.
②Calculated continuous current based on maximum allowable junction temperature.
③When mounted on 1 inch square copper board, t≤10sec. The value in any given application depends on the user's specific board design.
④Limited by T_{Jmax} ,starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = 10A, V_{GS} =10V.
⑤Pulse test;Pulse width≤300μs, duty cycle≤2%.
⑥Guaranteed by design, not subject to production testing.

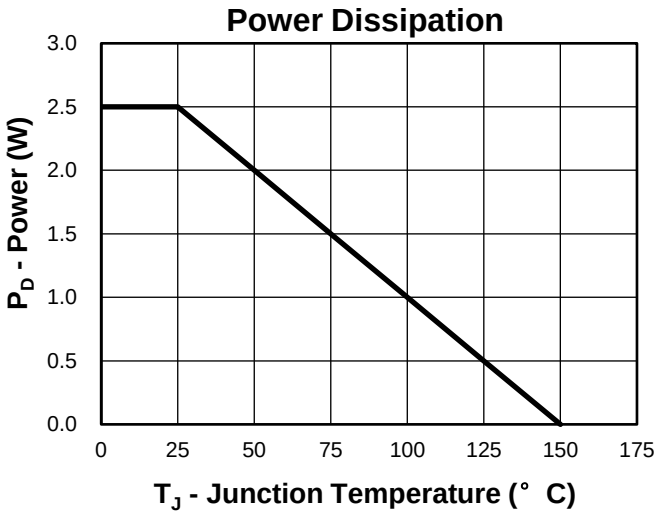
Ordering and Marking Information

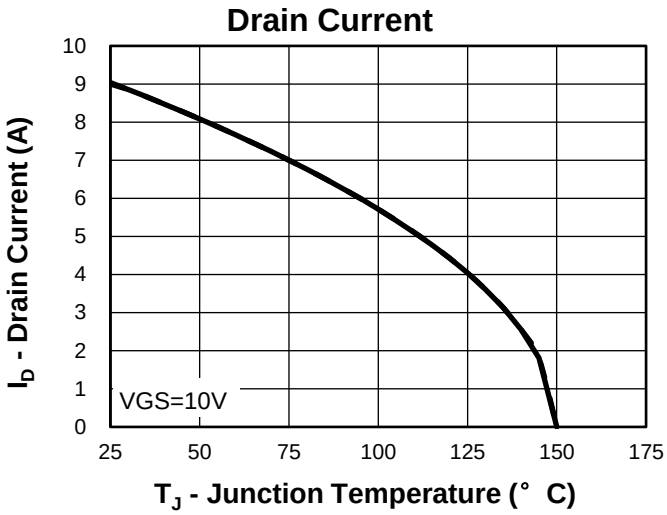
Device	Package	Packaging	Quantity	Reel Size	Tape width
KS1210HAT	SOP8	Tape&Reel	3000	13''	12mm

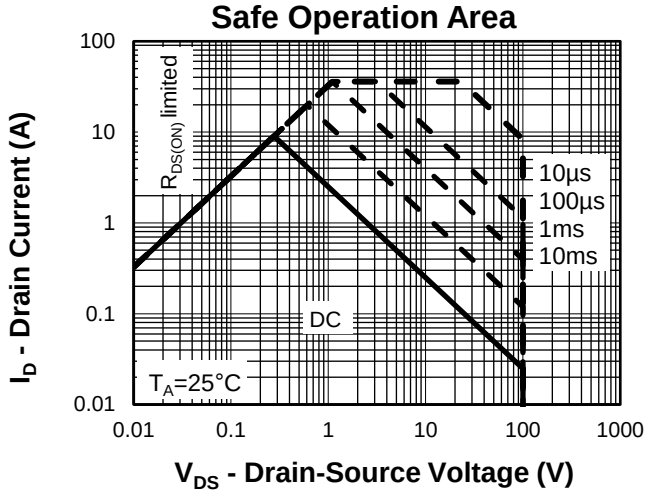


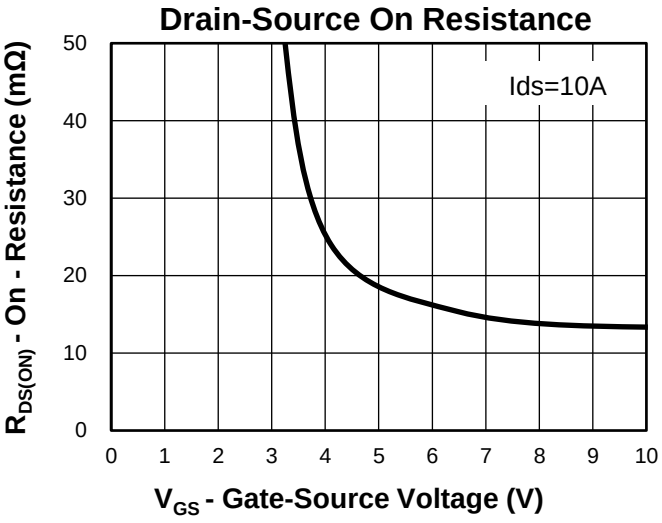
1st Line: Kwansemi LOGO， Kwansemi Code(KS)
2nd Line: Part Number(1210T)
3rd Line: Lot Number(YWWXXX)

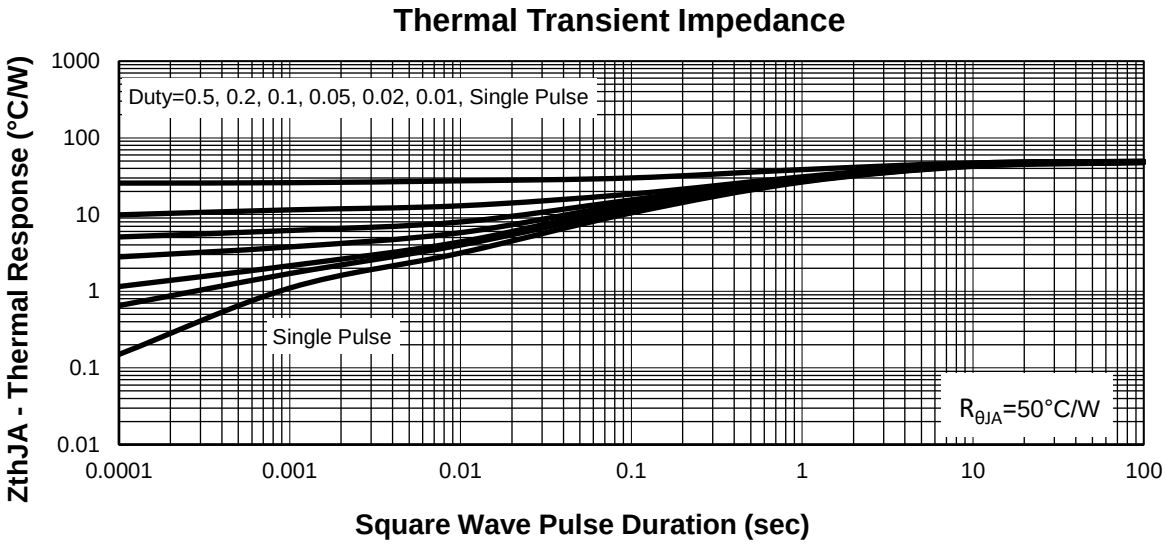
Typical Characteristics



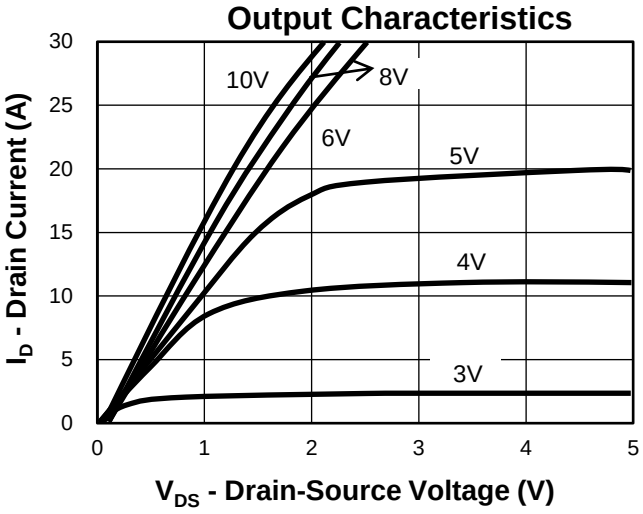


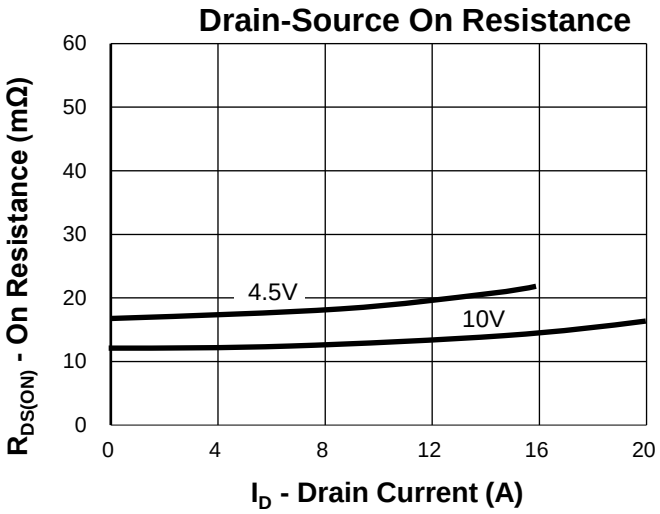


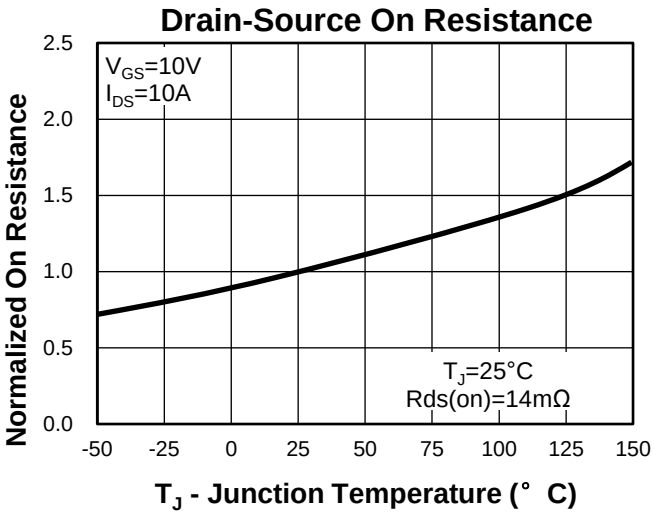


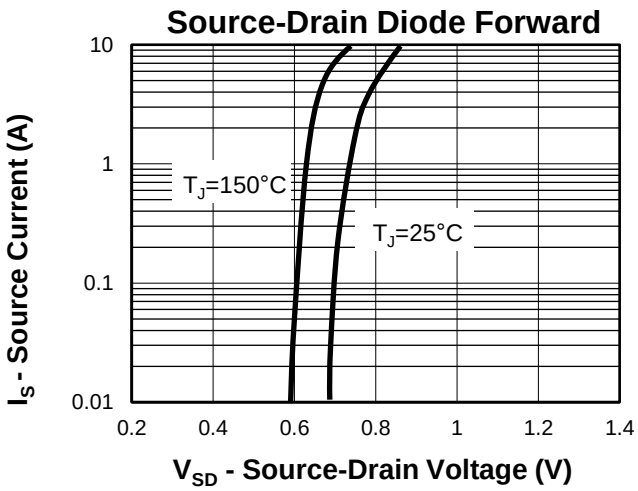


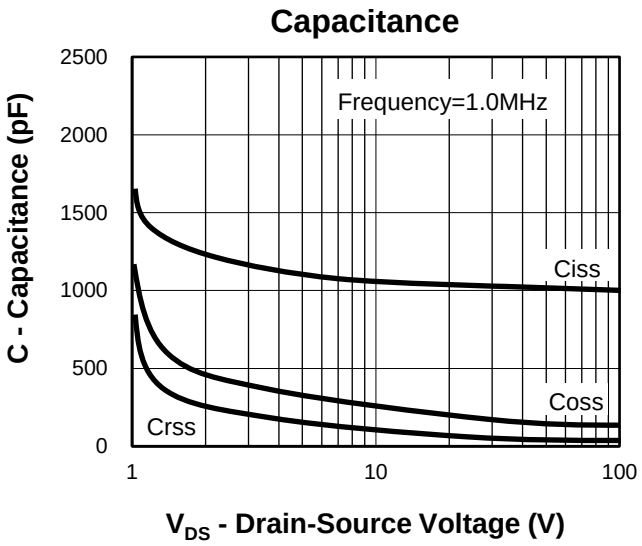
Typical Characteristics

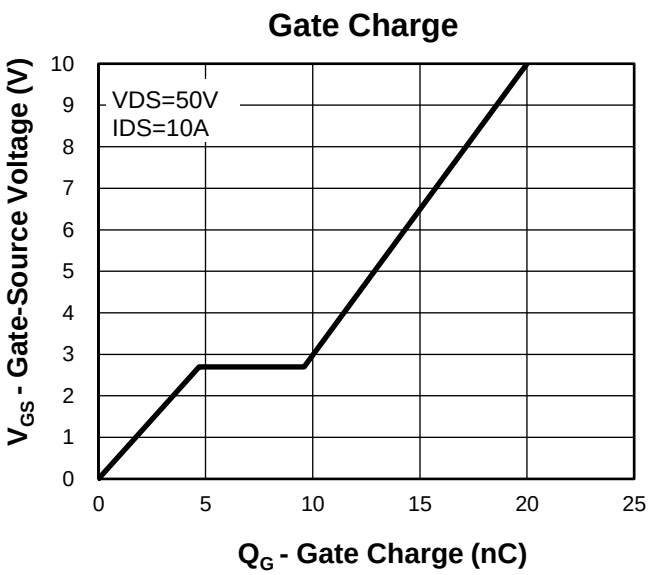












Package Information

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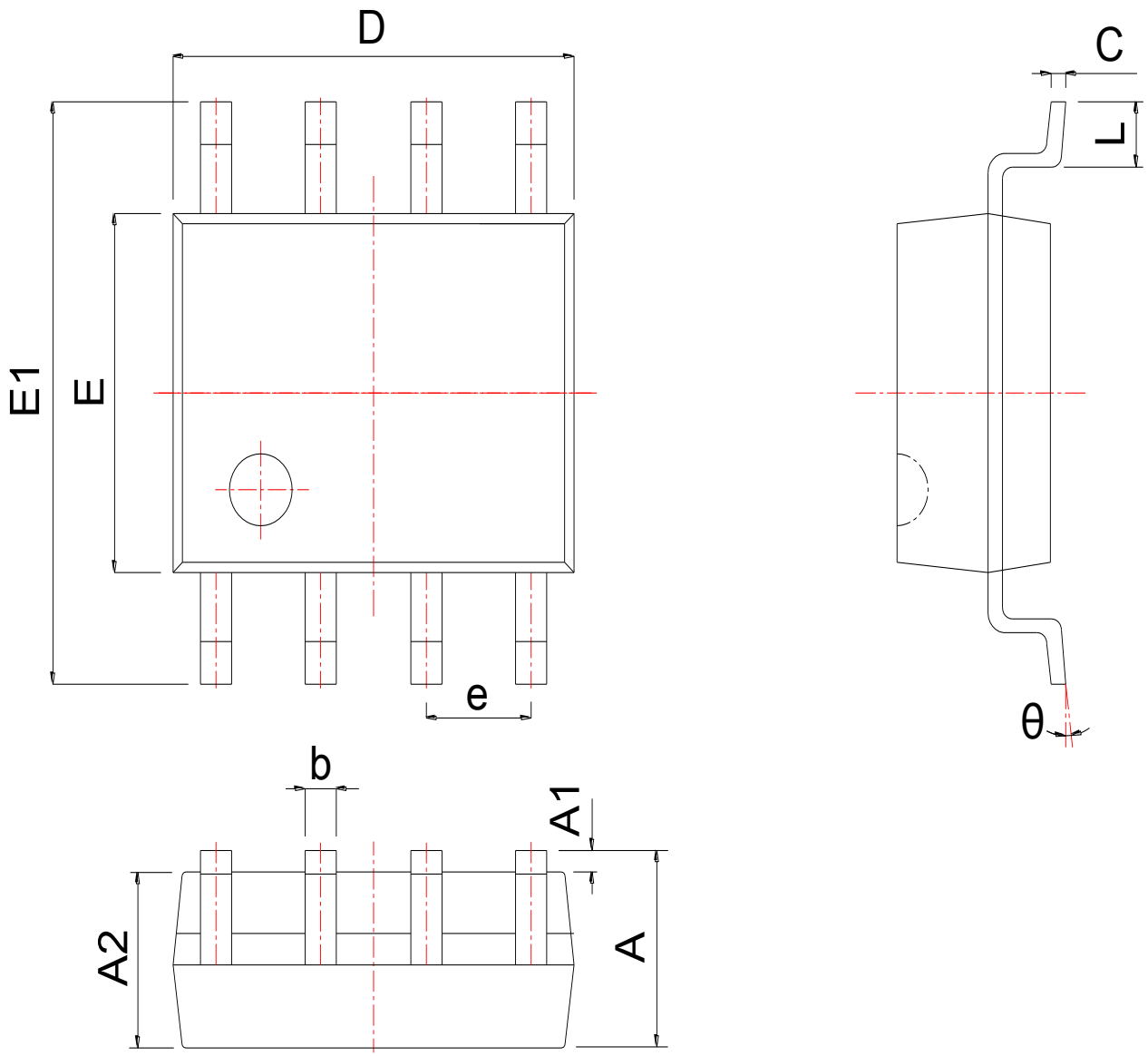
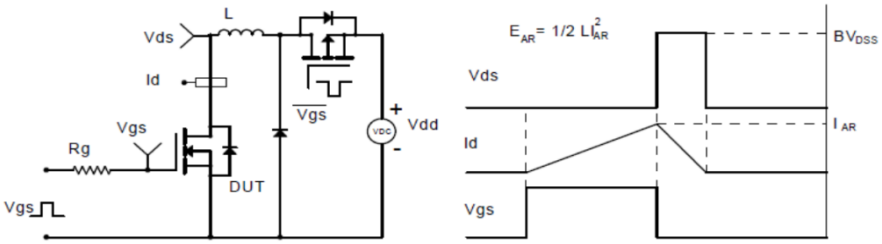
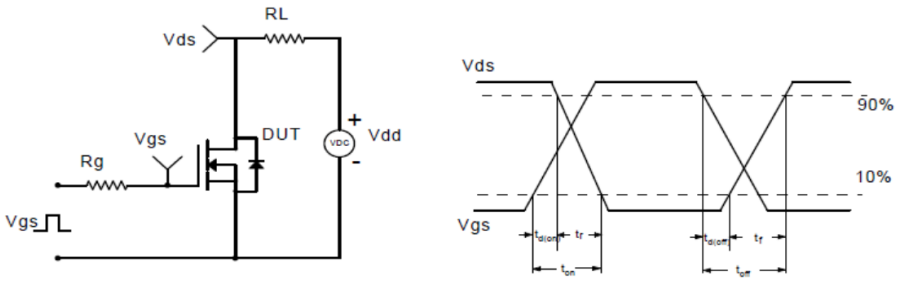


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.300	1.525	1.750	0.051	0.060	0.069
A1	0.050	0.150	0.250	0.002	0.006	0.010
A2	1.350	1.450	1.550	0.053	0.057	0.061
b	0.330	0.420	0.510	0.013	0.017	0.020
c	0.170	0.210	0.250	0.007	0.008	0.010
D	4.700	4.900	5.100	0.185	0.193	0.201
E	3.800	3.900	4.000	0.150	0.154	0.157
E1	5.800	6.000	6.200	0.228	0.236	0.244
e	1.270 BSC			0.050 BSC		
L	0.400	0.835	1.270	0.016	0.033	0.050
θ	0°		8°	0°		8°

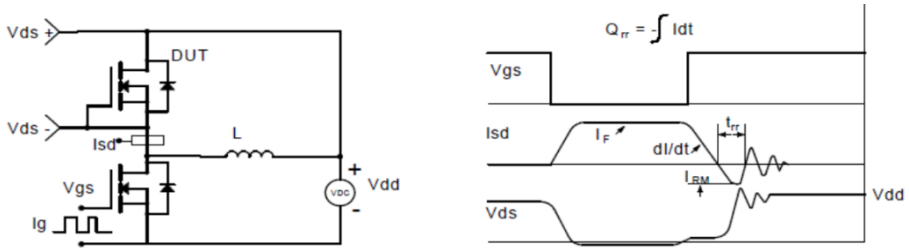
Avalanche Test Circuit and Waveforms



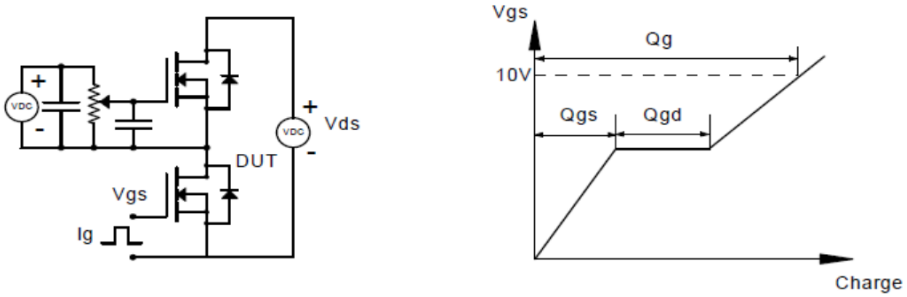
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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